

## IN THE CLAIMS

1. (Currently Amended) A high frequency dielectric ceramics composition constituted by combining a combination of  $(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  and  $y\text{TiO}_2$  as a main component, into which one of 0~5 wt %  $\text{B}_2\text{O}_3$ , 0~5 wt %  $\text{H}_3\text{BO}_3$ , 0~5 wt %  $\text{SiO}_2\text{-K}_2\text{O}$  glass, 0~5 wt %  $\text{B}_2\text{O}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass, or 0~5 wt %  $\text{H}_3\text{BO}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass is added as an additive, satisfies conditions of M is Mg, Co or Ni, 'x' is  $[0 \leq x \leq 0.55]$   $0 < x \leq 0.55$  in case of Mg and 'x' is  $[0 \leq x \leq 1.0]$   $0 < x \leq 1.0$  in case of Co, and  $[0 \leq x \leq 1.0]$   $0 < x \leq 1.0$  in case of Ni, and  $[0 \leq y \leq 0.6]$   $0 < y \leq 0.6$ .

2. (Original) A high frequency dielectric ceramics composition preparation method in which material powder of ZnO, MO (in this respect, MO is MgO, CoO or NiO) and  $\text{TiO}_2$  is weighed according to a composition range of  $(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  and  $y\text{TiO}_2$  (M is one of Mg, Co and Ni, x is  $0 \leq x \leq 0.55$  in case of Mg, x is  $0 \leq x \leq 1$  in case of Co, x is  $0 \leq x \leq 1$  in case of Ni, and y is  $0 \leq y \leq 0.6$ ), mixed and dried,

the dried powder is calcined at a temperature of 850~950°C,

the calcined powder is mixed with one of 0~5 wt %  $\text{B}_2\text{O}_3$ , 0~5 wt %  $\text{H}_3\text{BO}_3$ , 0~5 wt %  $\text{SiO}_2\text{-K}_2\text{O}$  glass, 0~5 wt %  $\text{B}_2\text{O}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass, or 0~5 wt %  $\text{H}_3\text{BO}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass as an additive,

the mixed powder is crushed,

the crushed power is shaped,

the shaped body is fired at a temperature of 800~925°C, and

$(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  is calcined at a temperature corresponding to a region (region II) of below a phase dissociation temperature as shown in Figure 1 to obtain  $(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  (M is Mg, Co or Ni) of a single phase of rhombohedral/hexagonal crystal.

3. (Original) The method of claim 2, wherein the shaped body is made in a manner that an aqueous solution adding a PVA binder is sprayed onto the crushed powder to make a granule, to which a pressure is applied.

4. (Original) The method of claim 3, further comprises a step for maintaining the shaped body at a temperature of 300~500°C for a predetermined time and removing the binder.

5. (Original) The method of claim 2, wherein  $(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  is first calcined, and the calcined  $(\text{Zn}_{1-x}\text{M}_x)\text{TiO}_3$  is mixed with one of 0~5 wt %  $\text{B}_2\text{O}_3$ , 0~5 wt %  $\text{H}_3\text{BO}_3$ , 0~5 wt %  $\text{SiO}_2\text{-K}_2\text{O}$  glass, 0~5 wt %  $\text{B}_2\text{O}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass, or 0~5 wt %  $\text{H}_3\text{BO}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass as an additive, and then fired.

6. (Currently Amended) A high frequency dielectric ceramics composition constituted by combining a combination  $(\text{Zn}_{1-a}\text{Mg}_{1-b}\text{Co}_{1-c}\text{Ni}_{1-d})\text{TiO}_3$  and  $y\text{TiO}_2$  as a main component, into which one of 0~5 wt %  $\text{B}_2\text{O}_3$ , 0~5 wt %  $\text{H}_3\text{BO}_3$ , 0~5 wt %  $\text{SiO}_2\text{-K}_2\text{O}$  glass, 0~5 wt %  $\text{B}_2\text{O}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass, or 0~5 wt %  $\text{H}_3\text{BO}_3$  and  $\text{SiO}_2\text{-K}_2\text{O}$  glass is added as an additive,

satisfies conditions of  $[0 \leq a \leq 1, 0 \leq b \leq 1, 0 \leq c \leq 1, 0 \leq d \leq 1 \text{ and } 0 \leq y \leq 0.6]$   $0 < a \leq 1, 0 < b \leq 1, 0 < c \leq 1,$   
 $0 < d \leq 1 \text{ and } 0 < y \leq 0.6.$

7. (Currently Amended) ~~Various high frequency devices such as a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low temperature sintered board, a resonator and a filter or a ceramic antenna, are fabricated by using the dielectric~~ High frequency devices comprising the composition of claim 1.

8. (New) The high frequency devices of claim 7, wherein the high frequency devices are selected from the group consisting of a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low-temperature sintered board, a resonator, a filter, a ceramic antenna and combinations thereof.